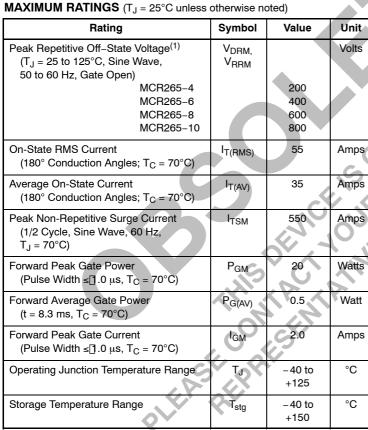
Preferred Device

# **Silicon Controlled Rectifiers**

# **Reverse Blocking Thyristors**

Designed for inverse parallel SCR output devices for solid state relays, welders, battery chargers, motor controls or applications requiring high surge operation.

- Photo Glass Passivated Blocking Junctions for High Temperature Stability, Center Gate for Uniform Parameters
- 550 Amperes Surge Capability
- Blocking Voltage to 800 Volts
- Device Marking: Logo, Device Type, e.g., MCR265-4, Date Code



(1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

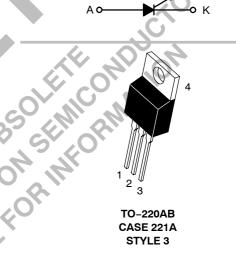
These devices are rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents.



# **ON Semiconductor**

http://onsemi.com

# SCRs **55 AMPERES RMS** 200 thru 800 VOLTS



PIN ASSIGNMENT		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

## **ORDERING INFORMATION**

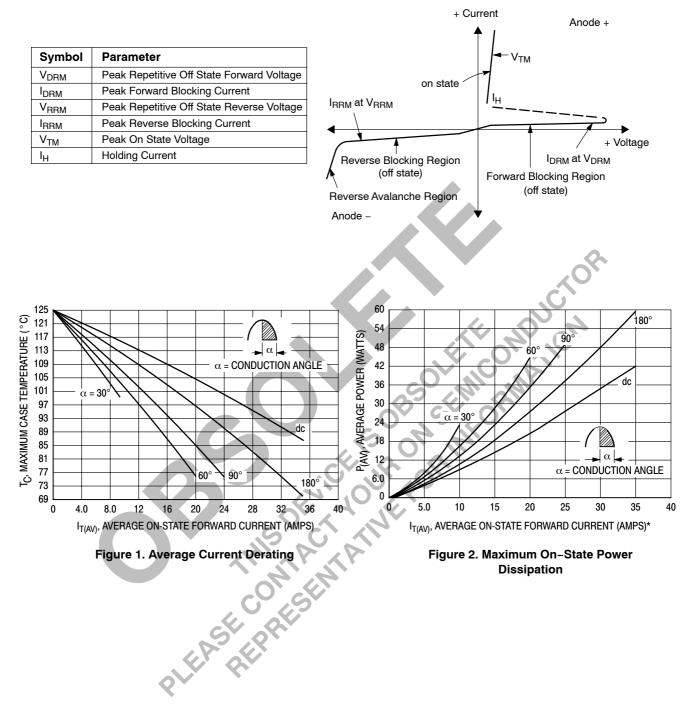
Device	Package	Shipping		
MCR265-4	TO220AB	500/Box		
MCR265-6	TO220AB	500/Box		
MCR265-8	TO220AB	500/Box		
MCR265-10	TO220AB	500/Box		

Preferred devices are recommended choices for future use and best overall value.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.9	°C/W	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	60	0	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C	
ELECTRICAL CHARACTERISTICS (T <sub>C</sub> = 25°C unless otherwise noted.)	·	•		
Characteristic St	/mbol Min	Тур	Max	Unit
OFF CHARACTERISTICS				
$ \begin{array}{l} \mbox{Peak Repetitive Forward or Reverse Blocking Current} & I_{DR} \\ (V_{AK} = Rated V_{DRM} \mbox{ or } V_{RRM}, \mbox{ Gate Open}) & T_J = 25^{\circ} C \\ T_J = 125^{\circ} C \end{array} $	M, I <sub>RRM</sub>		10 2.0	μA mA
ON CHARACTERISTICS				
Peak Forward On-State Voltage <sup>(1)</sup> (I <sub>TM</sub> = 110 A)	V <sub>TM</sub> –	1.5	1.9	Volts
Gate Trigger Current (Continuous dc) $(V_{AK} = 12 \text{ Vdc}, \text{ R}_{L} = 100 \text{ Ohms})$ $(T_{C} = -40^{\circ}\text{C})$	I <sub>GT</sub>	20 40	50 90	mA
Gate Trigger Voltage (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	V <sub>GT</sub> —	1.0	1.5	Volts
Gate Non-Trigger Voltage (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>J</sub> = 125°C)	V <sub>GD</sub> 0.2	<u>~</u> 0.	—	Volts
Holding Current (V <sub>AK</sub> = 12 Vdc, Initiating Current = 200 mA, Gate Open)	l <sub>H</sub> –	30	75	mA
Turn-On Time (I <sub>TM</sub> = 55 A, I <sub>GT</sub> = 200 mAdc)	t <sub>gt</sub>	1.5	—	μs
OYNAMIC CHARACTERISTICS	I. R.			
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform)	dv/dt —	50		V/μs
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform) 1) Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.				

## Voltage Current Characteristic of SCR



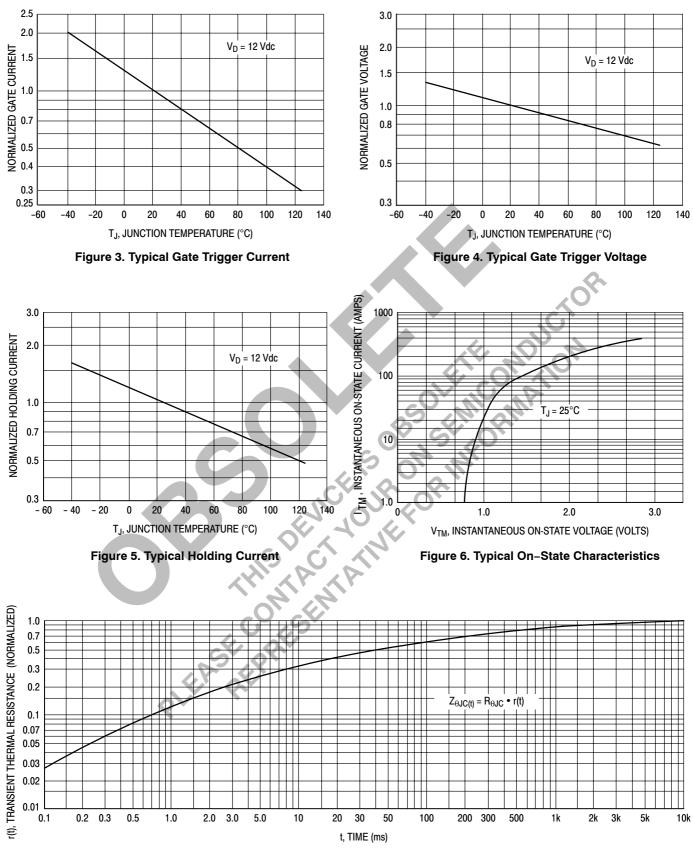
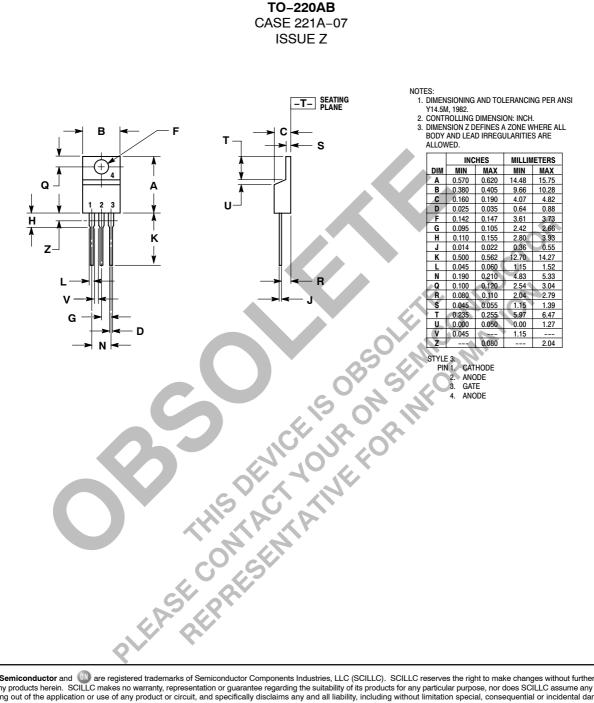


Figure 7. Thermal Response

#### PACKAGE DIMENSIONS



ON Semiconductor and images are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product cate a stuation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use payes that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit//Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

#### N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850

### ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative